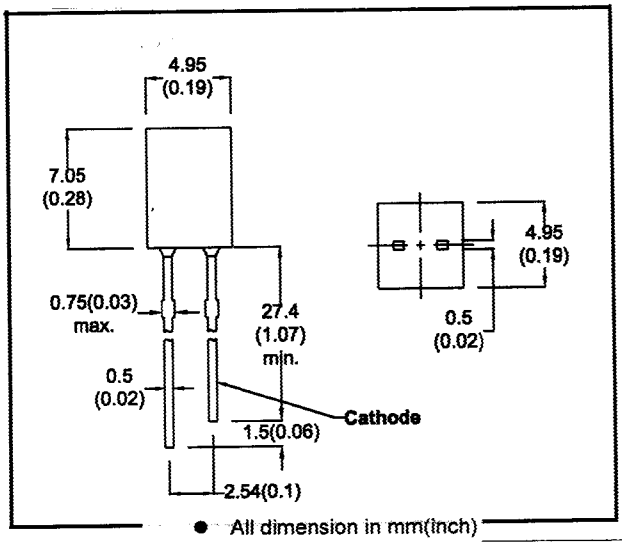
MICRO ELECTRONICS

MSB68DA
MRB68D
MOB68D
MOB68DR
MGB68D
MYB68D

DESCRIPTION

This series of solid state indicators are encapsulated in 4.95mm x 4.95mm rectangular package.

MSB68D is a GaP red chip with red diffused lens.
MSB68DA is a GaAlAs red chip with red diffused lens.
MRB68D is a GaAsP red chip with red diffused lens.
MOB68D is a GaAsP orange chip with orange diffused lens.
MOB68DR is high efficiency red chip with red diffused lens.
MGB68D is a GaP green chip with green diffused lens.
MYB68D is a GaAsP yellow chip with yellow diffused lens.



- All dimension in mm(inch)
- No Scale
- Tol. : +/-0.3mm

ABSOLUTE MAXIMUM RATINGS

	MSB68D	MSB68DA	MRB68D	MOB68D	MOB68DR	MGB68D	MYB68D	UNIT
Power Dissipation @ Ta=25°C	40	95	80	90	90	90	60	mW
Forward Current, DC (IF)	15	40	40	30	30	30	20	mA
Reverse Voltage	5	5	5	5	5	5	5	V
Operating & Storage Temperature Range	-55 to +100							°C
Lead Soldering Temperature (1/16" from body)	260							°C

ELECTRO-OPTICAL CHARACTERISTIC (Ta=25°C)

PARAMETER		SYMBOL	MSB68D	MSB68DA	MRB68D	MOB68D	MOB68DR	MGB68D	MYB68D	UNIT	CONDITIONS
Forward Voltage	TYP	VF	2.2	1.8	1.7	2.0	2.0	2.2	2.1	V	IF=20mA
	MAX		3.0	2.4	2.0	3.0	3.0	3.0	3.0		IF=20mA
Reverse Breakdown Voltage	MIN	BVR	5	5	5	5	5	5	5	V	IR=100μA
Luminous Intensity	MIN	IV	0.5*	4.2	0.4	2.6	2.6	3.8	2.2	mcd	IF=20mA
	TYP		0.65*	6	0.55	4.2	4.2	5	2.8	mcd	IF=20mA
Peak Wavelength	TYP	λp	700	660	660	630	640	570	585	nm	IF=20mA
Spectral Line Half Width	TYP	Δλ	100	20	20	35	35	35	35	nm	IF=20mA

* IV @ IF=10mA.

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